NSN 5962-01-099-6382

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View Online at https://aerobasegroup.com/nsn/5962-01-099-6382
Body Length:
0.925 inches
Body Width:
0.302 inches
Body Height:
0.175 inches
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and burn in and bipolar
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
12 input
Current Rating Per Characteristic:
140.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
7.0 volts power source
Capitance Rating Per Characteristic:
5.00 input picofarads and 8.00 output picofarads
Time Rating Per Chacteristic:
80.00 nanoseconds delay
Memory Device Type:
Prom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
18 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:

Yes - demil/mli

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